Amplifier Transistor NPN Silicon



ON Semiconductor®

MAXIMUM RATINGS

Collector – Emitter Voltage V _{CEO} 120 Vdc
Collector – Base Voltage V _{CBO} 140 Vdc
Emitter – Base Voltage V _{EBO} 5.0 Vdc
Collector Current — Continuous I _C 150 mAdc
Total Device Dissipation @ $T_A = 25^{\circ}C$ PD625mWDerate above 25^{\circ}C5.0mW/°C
Total Device Dissipation @ $T_C = 25^{\circ}C$ P_D 1.5WDerate above $25^{\circ}C$ 12mW/°C
Operating and Storage Junction Temperature RangeT_J, T_{stg}-55 to +150°C
THERMAL CHARACTERISTICS
Characteristic Symbol Max Unit
Thermal Resistance, Junction to Ambient R _{θJA} 200 °C/W
Thermal Resistance, Junction to Case R _{0JC} 83.3 °C/W

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

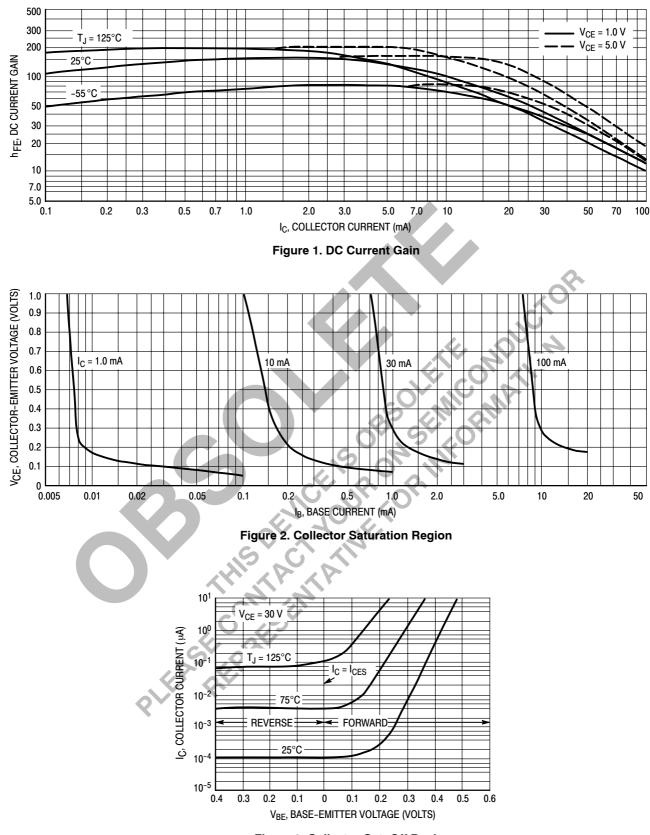
Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector – Emitter Breakdown Voltage ⁽¹⁾ ($I_C = 1.0 \text{ mAdc}, I_B = 0$)	V _{(BR)CEO}	120	_	Vdc
Collector – Base Breakdown Voltage $(I_C = 100 \ \mu Adc, I_E = 0)$	V _{(BR)CBO}	140	_	Vdc
Emitter – Base Breakdown Voltage (I _E = 10 μAdc, I _C = 0)	V _{(BR)EBO}	5.0	_	Vdc
Collector Cutoff Current (V _{CB} = 75 Vdc, I _E = 0)	I _{CBO}	—	1.0	μAdc
Emitter Cutoff Current (V _{EB} = 4.0 Vdc, I _C = 0)	I _{EBO}		100	nAdc

1. Pulse Test: Pulse Width = 300 $\mu s,$ Duty Cycle = 2.0%.

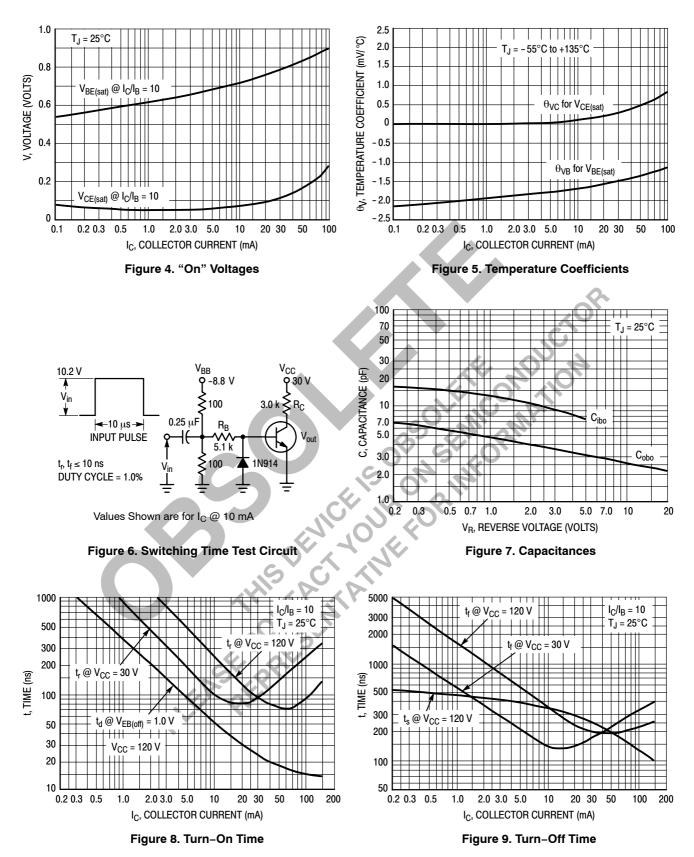
ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted) (Continued)

Characteristic	Symbol	Min	Max	Unit
ON CHARACTERISTICS				
DC Current Gain ⁽¹⁾ (I _C = 10 mAdc, V _{CE} = 5.0 Vdc)	h _{FE}	50	300	
Collector – Emitter Saturation Voltage ($I_C = 10 \text{ mAdc}, I_B = 1.0 \text{ mAdc}$) ($I_C = 50 \text{ mAdc}, I_B = 5.0 \text{ mAdc}$)	V _{CE(sat)}		0.20 0.30	Vdc
Base – Emitter Saturation Voltage ($I_C = 10 \text{ mAdc}, I_B = 1.0 \text{ mAdc}$) ($I_C = 50 \text{ mAdc}, I_B = 5.0 \text{ mAdc}$) ⁽¹⁾	V _{BE(sat)}		1.2 1.4	Vdc
SMALL-SIGNAL CHARACTERISTICS				
Current – Gain — Bandwidth Product ⁽¹⁾	fT	60	_	MHz

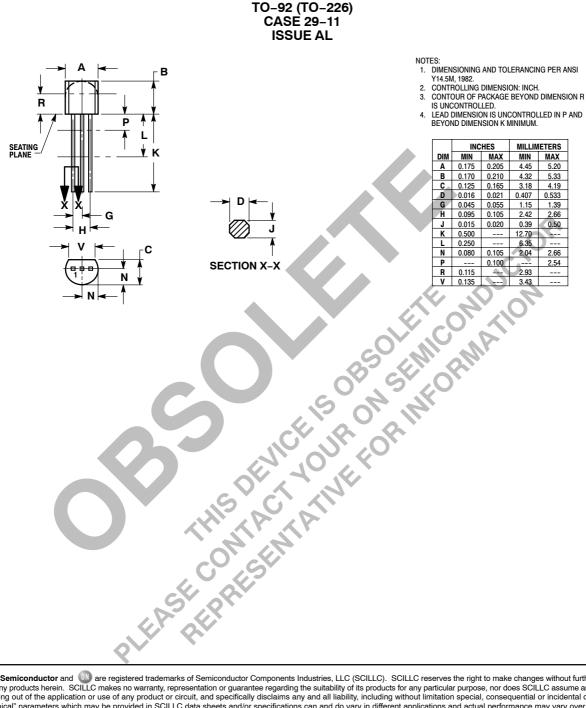
Current – Gain — Bandwidth Product ⁽¹⁾ ($I_C = 10 \text{ mAdc}, V_{CE} = 10 \text{ Vdc}, f = 20 \text{ MHz}$)	fT	60	_	MHz
Collector-Base Capacitance ($V_{CB} = 10 \text{ Vdc}, I_E = 0, f = 1.0 \text{ MHz}$)	C _{cb}		8.0	pF
Small–Signal Current Gain (I _C = 1.0 mAdc, V _{CE} = 10 Vdc, f = 1.0 kHz)	h _{fe}	30	Ċ,	—
(V _{CB} = 10 Vdc, I _E = 0, f = 1.0 MHz) Small–Signal Current Gain (I _C = 1.0 mAdc, V _{CE} = 10 Vdc, f = 1.0 kHz) 1. Pulse Test: Pulse Width = 300 μs, Duty Cycle = 2.0%.	ENCO ENTOP	ADUC	^N	







PACKAGE DIMENSIONS



ON Semiconductor and are registered trademarks of Semiconductor Components Industries, LLC (SCILLC). SCILLC reserves the right to make changes without further notice to any products herein. SCILLC makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does SCILLC assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. "Typical" parameters which may be provided in SCILLC data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. SCILLC does not convey any license under its patent rights nor the rights of others. SCILLC products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other application in which the failure of the SCILLC product could create a situation where personal injury or death may occur. Should Buyer purchase or use SCILLC products for any such unintended or unauthorized application, Buyer shall indemnify and hold SCILLC and its officers, employees, subsidiaries, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death agsociated with such unintended or unauthorized use payers that SCILLC was negligent regarding the design or manufacture of the part. SCILLC is an Equal Opportunit//Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:

Literature Distribution Center for ON Semiconductor P.O. Box 5163, Denver, Colorado 80217 USA Phone: 303–675–2175 or 800–344–3860 Toll Free USA/Canada Fax: 303–675–2176 or 800–344–3867 Toll Free USA/Canada Email: orderlit@onsemi.com N. American Technical Support: 800–282–9855 Toll Free USA/Canada Europe, Middle East and Africa Technical Support:

Phone: 421 33 790 2910 Japan Customer Focus Center Phone: 81–3–5773–3850 ON Semiconductor Website: www.onsemi.com

Order Literature: http://www.onsemi.com/orderlit

For additional information, please contact your local Sales Representative